

Jamie D Phillips

List of Publications by Year in descending order

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176
papers

4,840
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101384

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63
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180
all docs

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docs citations

180
times ranked

4011
citing authors

#	ARTICLE	IF	CITATIONS
1	A Light-Tolerant Wireless Neural Recording IC for Motor Prediction With Near-Infrared-Based Power and Data Telemetry. IEEE Journal of Solid-State Circuits, 2022, 57, 1061-1074.	3.5	19
2	Effects of high temperature annealing on the atomic layer deposited HfO ₂ / ¹² -Ga ₂ O ₃ (010) interface. Journal of Applied Physics, 2022, 131, .	1.1	10
3	Tracking the Migration of the Monarch Butterflies with the World's Smallest Computer. GetMobile (New York, N Y), 2022, 26, 25-29.	0.7	0
4	A low-power communication scheme for wireless, 1000 channel brain-machine interfaces. Journal of Neural Engineering, 2022, 19, 036037.	1.8	6
5	Thermoradiative Cell Equivalent Circuit Model. IEEE Transactions on Electron Devices, 2021, 68, 928-930.	1.6	4
6	Charge trapping and recovery in ALD HfO ₂ / ¹² -Ga ₂ O ₃ (010) MOS capacitors. Semiconductor Science and Technology, 2021, 36, 04LT01.	1.0	5
7	Energy Harvesting in Nanosystems: Powering the Next Generation of the Internet of Things. Frontiers in Nanotechnology, 2021, 3, .	2.4	19
8	Bridging the "Last Millimeter" Gap of Brain-Machine Interfaces via Near-Infrared Wireless Power Transfer and Data Communications. ACS Photonics, 2021, 8, 1430-1438.	3.2	23
9	Memristors Based on (Zr, Hf, Nb, Ta, Mo, W) High-Entropy Oxides. Advanced Electronic Materials, 2021, 7, 2001258.	2.6	22
10	A Light Tolerant Neural Recording IC for Near-Infrared-Powered Free Floating Motes. , 2021, 2021, .		7
11	Mid-wave infrared transmittance filters in suspended GaAs subwavelength gratings. Applied Physics Letters, 2021, 119, 031103.	1.5	3
12	Highly selective GaAs/AlGaAs dry etching using HBr/SF ₆ /He. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2021, 39, 052202.	0.6	1
13	A Stacked-Photovoltaic-Cell Energy Harvester with >81% Indoor Light Harvesting Efficiency for Millimeter-Scale Energy-Autonomous Sensor Nodes. , 2021, , .		0
14	mSAIL. , 2021, , .		4
15	Dual-Junction GaAs Photovoltaics for Low Irradiance Wireless Power Transfer in Submillimeter-Scale Sensor Nodes. IEEE Journal of Photovoltaics, 2020, 10, 1721-1726.	1.5	6
16	Demonstration of a $G \times aS \times b$ Quantum Dot Intermediate Band Solar Cell Operating at Maximum Power Point. Physical Review Letters, 2020, 125, 247703.	2.9	11
17	26.9 A 0.19 Å ² —0.17mm ² Wireless Neural Recording IC for Motor Prediction with Near-Infrared-Based Power and Data Telemetry. , 2020, 2020, 416-418.		29
18	Mid-wave infrared filtering in silicon subwavelength zero-contrast gratings. , 2020, , .		3

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19	Polarization-independent narrowband transmittance filters via symmetry-protected modes in high contrast gratings. <i>Optics Letters</i> , 2020, 45, 4348.	1.7	16
20	InGaAs/GaAsSb Type-II Superlattices for Short-Wavelength Infrared Detection. <i>Journal of Electronic Materials</i> , 2019, 48, 6025-6029.	1.0	8
21	Carrier dynamics of intermediate sub-bandgap transitions in ZnTeO. <i>Journal of Applied Physics</i> , 2019, 126, 135701.	1.1	2
22	Surface morphology and straight crack generation of ultrafast laser irradiated \hat{I}^2 -Ga ₂ O ₃ . <i>Journal of Applied Physics</i> , 2019, 125, 223104.	1.1	12
23	Ternary Alloy Rare-Earth Scandate as Dielectric for Ga_2O_3 MOS Structures. <i>IEEE Transactions on Electron Devices</i> , 2019, 66, 2489-2495.	1.6	21
24	High-efficiency photovoltaic modules on a chip for millimeter-scale energy harvesting. <i>Progress in Photovoltaics: Research and Applications</i> , 2019, 27, 540-546.	4.4	17
25	Low damage electrical modification of 4H-SiC via ultrafast laser irradiation. <i>Journal of Applied Physics</i> , 2018, 123, .	1.1	12
26	A 179-Lux Energy-Autonomous Fully-Encapsulated 17-mm ³ Sensor Node with Initial Charge Delay Circuit for Battery Protection. , 2018, , .		8
27	Influence of Subwavelength Grating Asymmetry on Long-Wavelength Infrared Transmittance Filters. <i>IEEE Photonics Journal</i> , 2018, 10, 1-8.	1.0	3
28	Influence of Finite Grating Size on Guided Mode Resonance Transmission Filters. , 2018, , .		0
29	Analysis of Carrier Transport in n-Type Hg _{1-x} CdxTe with Ultra-Low Doping Concentration. <i>Journal of Electronic Materials</i> , 2018, 47, 5699-5704.	1.0	2
30	Subcutaneous Photovoltaic Infrared Energy Harvesting for Bio-implantable Devices. <i>IEEE Transactions on Electron Devices</i> , 2017, 64, 2432-2437.	1.6	65
31	Three-Bandgap Absolute Quantum Efficiency in GaSb/GaAs Quantum Dot Intermediate Band Solar Cells. <i>IEEE Journal of Photovoltaics</i> , 2017, 7, 508-512.	1.5	21
32	Analysis of the intermediate-band absorption properties of type-II GaSb/GaAs quantum-dot photovoltaics. <i>Physical Review B</i> , 2017, 96, .	1.1	32
33	Infrared Energy Harvesting in Millimeter-Scale GaAs Photovoltaics. <i>IEEE Transactions on Electron Devices</i> , 2017, 64, 4554-4560.	1.6	12
34	Variable-Field Hall Effect Analysis of HgCdTe Epilayers with Very Low Doping Density. <i>Journal of Electronic Materials</i> , 2017, 46, 5479-5483.	1.0	2
35	Small-Area Si Photovoltaics for Low-Flux Infrared Energy Harvesting. <i>IEEE Transactions on Electron Devices</i> , 2017, 64, 15-20.	1.6	18
36	Leaky mode coupling in asymmetric subwavelength dielectric gratings. , 2017, , .		0

#	ARTICLE	IF	CITATIONS
37	Notice of Removal Three-bandgap absolute quantum efficiency in intermediate band solar cells. , 2017, , .		0
38	Long-wavelength infrared transmission filters via two-step subwavelength dielectric gratings. Optics Letters, 2017, 42, 518.	1.7	12
39	The effect of doping on low temperature growth of high quality GaAs nanowires on polycrystalline films. Nanotechnology, 2016, 27, 495605.	1.3	3
40	21.4 A >78%-efficient light harvester over 100-to-100klux with reconfigurable PV-cell network and MPPT circuit. , 2016, 2016, 370-371.		32
41	Narrowband infrared transmission filters via asymmetric subwavelength dielectric gratings. , 2016, , .		0
42	Energy Harvesting for GaAs Photovoltaics Under Low-Flux Indoor Lighting Conditions. IEEE Transactions on Electron Devices, 2016, 63, 2820-2825.	1.6	49
43	Investigating Student Motivation and Performance in Electrical Engineering and Its Subdisciplines. IEEE Transactions on Education, 2016, 59, 241-247.	2.0	6
44	Chemical epitaxy and interfacial reactivity in solution deposited PbS on ZnTe. Journal of Materials Chemistry C, 2016, 4, 1996-2002.	2.7	6
45	AlGaAs Photovoltaics for Indoor Energy Harvesting in mm-Scale Wireless Sensor Nodes. IEEE Transactions on Electron Devices, 2015, 62, 2170-2175.	1.6	87
46	Heterojunction Band Offset Limitations on Open-Circuit Voltage in $ZnTe/TiO_2$ Solar Cells. IEEE Journal of Photovoltaics, 2015, 5, 874-877.	1.5	5
47	Normal incidence narrowband transmission filtering capabilities using symmetry-protected modes of a subwavelength, dielectric grating. Optics Letters, 2015, 40, 2637.	1.7	36
48	Dual color longwave InAs/GaSb type-II strained layer superlattice detectors. Infrared Physics and Technology, 2015, 70, 93-98.	1.3	8
49	Nanodot formation induced by femtosecond laser irradiation. Applied Physics Letters, 2014, 105, .	1.5	11
50	Intermediate Band to Conduction Band Optical Absorption in ZnTeO. IEEE Journal of Photovoltaics, 2014, 4, 1091-1094.	1.5	8
51	Passivation of long-wave infrared InAs/GaSb superlattice detectors with epitaxially grown ZnTe. , 2014, , .		3
52	Distinguishing Optical Behavior of Oxygen States and Native Deep Level Emission in ZnTe. Journal of Electronic Materials, 2014, 43, 879-883.	1.0	5
53	Oxygen Incorporation in ZnTeO Alloys via Molecular Beam Epitaxy. Journal of Electronic Materials, 2014, 43, 889-893.	1.0	5
54	Intrinsically switchable, high-Q ferroelectric-on-silicon composite film bulk acoustic resonators. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 2014, 61, 231-238.	1.7	32

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55	Indoor photovoltaic energy harvesting for mm-scale systems. , 2014, , .		3
56	Multiphoton Sub-Band-Gap Photoconductivity and Critical Transition Temperature in Type-II GaSb Quantum-Dot Intermediate-Band Solar Cells. Physical Review Applied, 2014, 1, .	1.5	32
57	Resolving spectral overlap issue of intermediate band solar cells using non-uniform sub-bandgap state filling. Progress in Photovoltaics: Research and Applications, 2014, 22, 1062-1069.	4.4	5
58	Transport properties of ZnTe:N thin films. Applied Physics Letters, 2013, 103, 042108.	1.5	7
59	Intrinsically Switchable Ferroelectric Contour Mode Resonators. IEEE Transactions on Microwave Theory and Techniques, 2013, 61, 2806-2813.	2.9	6
60	A New Class of Room-Temperature Multiferroic Thin Films with Bismuth-Based Supercell Structure. Advanced Materials, 2013, 25, 1028-1032.	11.1	78
61	Suspended Si/air high contrast subwavelength gratings for long-wavelength infrared reflectors. Proceedings of SPIE, 2013, , .	0.8	0
62	Intermediate band solar energy conversion in ZnTeO. , 2013, , .		2
63	Epitaxial growth of ZnTe on GaSb(100) using in situ ZnCl ₂ surface clean. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2013, 31, 03C118.	0.6	2
64	Preserving voltage and long wavelength photoresponse in GaSb/GaAs quantum dot solar cells. , 2013, , .		5
65	The disintegration of GaSb/GaAs nanostructures upon capping. Applied Physics Letters, 2013, 102, .	1.5	26
66	Broadband long-wavelength infrared Si/SiO ₂ subwavelength grating reflector. Optics Letters, 2012, 37, 1523.	1.7	20
67	Room temperature strong coupling effects from single ZnO nanowire microcavity. Optics Express, 2012, 20, 11830.	1.7	24
68	Intrinsically switchable thin film ferroelectric resonators. , 2012, , .		9
69	A DC voltage dependent switchable acoustically coupled BAW filter based on BST-on-silicon composite structure. , 2012, , .		6
70	Decoupling spectral overlap of intermediate band solar cells using low-high state filling. , 2012, , .		2
71	Room Temperature Polariton Lasing in a Single ZnO Nanowire Microcavity. , 2012, , .		0
72	Illumination instabilities in ZnO/HfO ₂ thin-film transistors and influence of grain boundary charge. Journal of Materials Research, 2012, 27, 2199-2204.	1.2	5

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73	Mid-wave infrared HgCdTe nBn photodetector. Applied Physics Letters, 2012, 100, .	1.5	114
74	Unipolar barrier-integrated HgCdTe infrared detectors. , 2012, , .		1
75	Design of an Auger-Suppressed Unipolar HgCdTe NB ¹ / ₂ N Photodetector. Journal of Electronic Materials, 2012, 41, 2886-2892.	1.0	44
76	Thermal emission in type-II GaSb/GaAs quantum dots and prospects for intermediate band solar energy conversion. Journal of Applied Physics, 2012, 111, 074514.	1.1	43
77	Bias-Temperature-Stress Characteristics of ZnO/HfO_2 Thin-Film Transistors. IEEE Transactions on Electron Devices, 2012, 59, 1488-1493.	1.6	13
78	Atomic Resolution TEM Study on Quantum Dots in ZnSe/ZnTe Heterostructure. Microscopy and Microanalysis, 2011, 17, 1646-1647.	0.2	0
79	ZnO nanorods for simultaneous light trapping and transparent electrode application in solar cells. , 2011, , .		1
80	Calculated performance of an Auger-suppressed unipolar HgCdTe photodetector for high temperature operation. , 2011, , .		1
81	Predicted Performance Improvement of Auger-Suppressed HgCdTe Photodiodes and p-n Heterojunction Detectors. IEEE Transactions on Electron Devices, 2011, 58, 501-507.	1.6	37
82	Intermediate-band solar cells based on dilute alloys and quantum dots. Frontiers of Optoelectronics in China, 2011, 4, 2-11.	0.2	6
83	Design and Modeling of HgCdTe nBn Detectors. Journal of Electronic Materials, 2011, 40, 1624-1629.	1.0	65
84	ZnO/ZnSe/ZnTe Heterojunctions for ZnTe-Based Solar Cells. Journal of Electronic Materials, 2011, 40, 1674-1678.	1.0	24
85	Admittance Spectroscopy of Interface States in ZnO/HfO_2 Thin-Film Electronics. IEEE Electron Device Letters, 2011, 32, 1713-1715.	2.2	7
86	Arsenic Diffusion Study in HgCdTe for Low p-Type Doping in Auger-Suppressed Photodiodes. Journal of Electronic Materials, 2010, 39, 945-950.	1.0	9
87	MWIR and LWIR HgCdTe Infrared Detectors Operated with Reduced Cooling Requirements. Journal of Electronic Materials, 2010, 39, 873-881.	1.0	31
88	An Intrinsically Switchable FBAR Filter Based on Barium Titanate Thin Films. IEEE Microwave and Wireless Components Letters, 2009, 19, 359-361.	2.0	33
89	Parameter extraction of HgCdTe infrared photodiodes exhibiting Auger suppression. Journal Physics D: Applied Physics, 2009, 42, 234003.	1.3	15
90	Drift-Diffusion Modeling for Impurity Photovoltaic Devices. IEEE Transactions on Electron Devices, 2009, 56, 3168-3174.	1.6	99

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91	Optical Characteristics of ZnTeO Thin Films Synthesized by Pulsed Laser Deposition and Molecular Beam Epitaxy. Journal of Electronic Materials, 2009, 38, 119-125.	1.0	44
92	Intermediate-band photovoltaic solar cell based on ZnTe:O. Applied Physics Letters, 2009, 95, .	1.5	199
93	Model for intermediate band solar cells incorporating carrier transport and recombination. Journal of Applied Physics, 2009, 105, 064512.	1.1	69
94	Generation and recombination rates at ZnTe:O intermediate band states. Applied Physics Letters, 2009, 95, .	1.5	51
95	Intrinsically switchable contour mode acoustic wave resonators based on barium titanate thin films. , 2009, , .		6
96	Complementary Thin-Film Electronics Based on n-Channel ZnO and p-Channel ZnTe. IEEE Electron Device Letters, 2009, 30, 1314-1316.	2.2	21
97	Frontiers in semiconductor-based devices. Journal Physics D: Applied Physics, 2009, 42, 230301-230301.	1.3	0
98	Optimization of random diffraction gratings in thin-film solar cells using genetic algorithms. Solar Energy Materials and Solar Cells, 2008, 92, 1689-1696.	3.0	98
99	Quantum Confinement and Carrier Localization Effects in ZnO/Mg _x Zn _{1-x} O Wells Synthesized by Pulsed Laser Deposition. Journal of Electronic Materials, 2008, 37, 749-754.	1.0	10
100	Modeling of LWIR HgCdTe Auger-Suppressed Infrared Photodiodes under Nonequilibrium Operation. Journal of Electronic Materials, 2008, 37, 1362-1368.	1.0	28
101	Electrical Characteristics and Photoresponse of ZnO/ZnTe Heterojunction Diodes. Journal of Electronic Materials, 2008, 37, 1044-1048.	1.0	21
102	A ferroelectric-based impedance tuner for adaptive matching applications. , 2008, , .		5
103	Growth and structural properties of m-plane ZnO on MgO (001) by molecular beam epitaxy. Applied Physics Letters, 2008, 92, 233505.	1.5	51
104	Hysteretic metal-ferroelectric semiconductor capacitors based on PZT/ZnO heterostructures. Journal Physics D: Applied Physics, 2007, 40, 2430-2434.	1.3	45
105	A DC Voltage Dependant Switchable Thin Film Bulk Wave Acoustic Resonator Using Ferroelectric Thin Film. IEEE MTT-S International Microwave Symposium Digest IEEE MTT-S International Microwave Symposium, 2007, , .	0.0	55
106	Improving Linearity of Ferroelectric-Based Microwave Tunable Circuits. IEEE Transactions on Microwave Theory and Techniques, 2007, 55, 354-360.	2.9	32
107	Electrical Characteristics of PEDOT:PSS Organic Contacts to HgCdTe. Journal of Electronic Materials, 2007, 36, 841-845.	1.0	9
108	Modeling and Design Considerations of HgCdTe Infrared Photodiodes under Nonequilibrium Operation. Journal of Electronic Materials, 2007, 36, 846-851.	1.0	26

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109	Sub-bandgap photoconductivity in ZnO epilayers and extraction of trap density spectra. Semiconductor Science and Technology, 2006, 21, 717-723.	1.0	133
110	A Linearity Improvement Technique for Thin-film Barium Strontium Titanate Capacitors. , 2006, , .		23
111	Analysis and design optimization of electrooptic interferometric modulators for microphotronics applications. Journal of Lightwave Technology, 2006, 24, 2340-2346.	2.7	13
112	Electric field dependence of piezoelectric coefficient in ferroelectric thin films. Journal of Electroceramics, 2006, 17, 613-617.	0.8	13
113	Free carrier absorption and lattice vibrational modes in bulk ZnO. Journal of Electronic Materials, 2006, 35, 525-529.	1.0	22
114	Trap-related photoconductivity in ZnO epilayers. Journal of Electronic Materials, 2006, 35, 543-549.	1.0	85
115	ZnO thin-film transistors with polycrystalline (Ba,Sr)TiO ₃ gate insulators. Applied Physics Letters, 2006, 88, 212903.	1.5	98
116	Properties of ferroelectric Pb(Zr,Ti)O ₃ thin films on ZnO/Al ₂ O ₃ (0001) epilayers. Thin Solid Films, 2005, 491, 301-304.	0.8	13
117	Growth and electronic properties of ZnO epilayers by plasma-assisted molecular beam epitaxy. Journal of Electronic Materials, 2005, 34, 699-703.	1.0	14
118	Detailed study of above bandgap optical absorption in HgCdTe. Journal of Electronic Materials, 2005, 34, 773-778.	1.0	43
119	Properties of electrical contacts on bulk and epitaxial n-type ZnO. Journal of Electronic Materials, 2005, 34, 389-394.	1.0	22
120	Optical waveguiding in BaTiO ₃ •MgO•AlxOy•GaAs heterostructures. Applied Physics Letters, 2004, 85, 5206-5208.	1.5	10
121	Epitaxial growth and surface modeling of ZnO on c-plane Al ₂ O ₃ . Applied Physics Letters, 2004, 85, 6338-6340.	1.5	9
122	Electronic properties of ferroelectric BaTiO ₃ •MgO capacitors on GaAs. Applied Physics Letters, 2004, 85, 3208-3210.	1.5	30
123	Optical-absorption model for molecular-beam epitaxy HgCdTe and application to infrared detector photoresponse. Journal of Electronic Materials, 2004, 33, 701-708.	1.0	20
124	Pulsed laser annealing of self-organized InAs/GaAs quantum dots. Journal of Electronic Materials, 2004, 33, L5-L8.	1.0	13
125	Optical absorption studies of HgCdTe epitaxial layers for improved infrared detector modeling. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 662-665.	0.8	0
126	Far infrared modulated photoluminescence in InSb quantum dots. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 22, 598-602.	1.3	1

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127	Optical absorption properties of HgCdTe epilayers with uniform composition. Journal of Electronic Materials, 2003, 32, 646-650.	1.0	19
128	Threading and misfit-dislocation motion in molecular-beam epitaxy-grown HgCdTe epilayers. Journal of Electronic Materials, 2003, 32, 710-716.	1.0	28
129	Absorption, carrier lifetime, and gain in InAs-GaAs quantum-dot infrared photodetectors. IEEE Journal of Quantum Electronics, 2003, 39, 459-467.	1.0	145
130	Deposition Of BaTiO3 Thin Films And MgO Buffer Layers On Patterned GaAs Substrates For Integrated Optics Applications. Materials Research Society Symposia Proceedings, 2003, 784, 11231.	0.1	0
131	Uniformity of optical absorption in HgCdTe epilayer measured by infrared spectromicroscopy. Applied Physics Letters, 2003, 83, 3701-3703.	1.5	19
132	Far-infrared modulated photoluminescence spectroscopy of InSb/GaSb quantum dot structures. Physical Review B, 2003, 68, .	1.1	14
133	Gain dynamics and ultrafast spectral hole burning in In(Ga)As self-organized quantum dots. Applied Physics Letters, 2002, 81, 670-672.	1.5	51
134	Lateral indium-indium pair correlations within the wetting layers of buried InAs/GaAs quantum dots. Applied Physics Letters, 2002, 81, 1423-1425.	1.5	13
135	Evaluation of the fundamental properties of quantum dot infrared detectors. Journal of Applied Physics, 2002, 91, 4590-4594.	1.1	246
136	Control of very-long-wavelength infrared HgCdTe detector-cutoff wavelength. Journal of Electronic Materials, 2002, 31, 664-668.	1.0	19
137	Advances in large-area Hg _{1-x} Cd _x Te photovoltaic detectors for remote-sensing applications. Journal of Electronic Materials, 2002, 31, 726-731.	1.0	12
138	Composition control of long wavelength MBE HgCdTe using In-situ spectroscopic ellipsometry. Journal of Electronic Materials, 2001, 30, 643-646.	1.0	19
139	Carrier dynamics in self-organized quantum dots and their application to long-wavelength sources and detectors. Journal of Crystal Growth, 2001, 227-228, 27-35.	0.7	25
140	Growth of HgCdTe for long-wavelength infrared detectors using automated control from spectroscopic ellipsometry measurements. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2001, 19, 1580.	1.6	18
141	Optoelectronic Device Applications of Self-Organized In(Ga,Al)As/Ga(Al)As Quantum Dots. Materials Research Society Symposia Proceedings, 2000, 618, 195.	0.1	0
142	Growth of InSb on GaAs using InAlSb buffer layers. Journal of Crystal Growth, 2000, 209, 567-571.	0.7	16
143	InAsSb/InPSb strained-layer superlattice growth using metal-organic chemical vapor deposition. Journal of Crystal Growth, 2000, 211, 400-404.	0.7	7
144	Exploring new active regions for type I InAsSb strained-layer lasers. Journal of Electronic Materials, 2000, 29, 91-93.	1.0	3

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145	Quantum dot carrier dynamics and far-infrared devices. , 2000, 4078, 84.		3
146	Growth and electroluminescent properties of self-organized In _{0.4} Ga _{0.6} As/GaAs quantum dots grown on silicon. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1999, 17, 1116.	1.6	3
147	Electron intersubband energy level spacing in self-organized In _{0.4} Ga _{0.6} As/GaAs quantum dot lasers from temperature-dependent modulation measurements. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena. 1999. 17. 1276.	1.6	2
148	Bistability and self-pulsation in quantum-dot lasers with intracavity quantum-dot saturable absorbers. Applied Physics Letters, 1999, 74, 1654-1656.	1.5	36
149	Pressure-induced energy level crossings and narrowing of photoluminescence linewidth in self-assembled InAlAs/AlGaAs quantum dots. Applied Physics Letters, 1999, 74, 1549-1551.	1.5	20
150	Nanometer-scale studies of vertical organization and evolution of stacked self-assembled InAs/GaAs quantum dots. Applied Physics Letters, 1999, 74, 2824-2826.	1.5	71
151	Self-organized In _{0.4} Ga _{0.6} As quantum-dot lasers grown on Si substrates. Applied Physics Letters, 1999, 74, 1355-1357.	1.5	79
152	Interdiffusion and surface segregation in stacked self-assembled InAs/GaAs quantum dots. Applied Physics Letters, 1999, 75, 2797-2799.	1.5	58
153	Bias-controlled wavelength switching in coupled-cavity In _{0.4} Ga _{0.6} As/GaAs self-organized quantum dot lasers. Applied Physics Letters, 1999, 74, 783-785.	1.5	31
154	In(Ga)As/GaAs self-organized quantum dot light emitters grown on silicon substrates. Journal of Crystal Growth, 1999, 201-202, 1186-1189.	0.7	2
155	Self-organized growth of In(Ga)As/GaAs quantum dots and their opto-electronic device applications. Bulletin of Materials Science, 1999, 22, 519-529.	0.8	6
156	In(Ga)As/GaAs self-organized quantum dot lasers: DC and small-signal modulation properties. IEEE Transactions on Electron Devices, 1999, 46, 871-883.	1.6	95
157	High-speed modulation of quantum-dot lasers. , 1999, , .		1
158	Self-assembled InAs-GaAs quantum-dot intersubband detectors. IEEE Journal of Quantum Electronics, 1999, 35, 936-943.	1.0	205
159	Temperature-dependent photoluminescence of In _{0.5} Al _{0.5} As/Al _{0.25} Ga _{0.75} As self-organized quantum dots. Journal of Applied Physics, 1999, 85, 2997-2999.	1.1	5
160	Characteristics of InAs/AlGaAs self-organized quantum dot modulation doped field effect transistors. Applied Physics Letters, 1998, 72, 3509-3511.	1.5	37
161	Far-infrared photoconductivity in self-organized InAs quantum dots. Applied Physics Letters, 1998, 72, 2020-2022.	1.5	229
162	Linear and quadratic electro-optic coefficients of self-organized In _{0.4} Ga _{0.6} As/GaAs quantum dots. Applied Physics Letters, 1998, 72, 1275-1277.	1.5	37

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163	Intersubband absorption and photoluminescence in Si-doped self-organized InAs/Ga(Al)As quantum dots. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1998, 16, 1343.	1.6	11
164	High-speed quantum well and quantum dot lasers. , 1998, 3547, 350.		1
165	Small-signal modulation and differential gain of single-mode self-organized In _{0.4} Ga _{0.6} As/GaAs quantum dot lasers. Applied Physics Letters, 1997, 70, 2952-2953.	1.5	86
166	Strain tensor, electronic spectra and carrier dynamics in In(Ga)As/GaAs self-assembled quantum dots. , 1997, , .		0
167	Photoluminescence and far-infrared absorption in Si-doped self-organized InAs quantum dots. Applied Physics Letters, 1997, 71, 2079-2081.	1.5	79
168	Room temperature luminescence from self-organized quantum dots with high size uniformity. Journal of Crystal Growth, 1997, 175-176, 720-724.	0.7	23
169	Room-temperature operation of In _{0.4} Ga _{0.6} As/GaAs self-organised quantum dot lasers. Electronics Letters, 1996, 32, 1374.	0.5	211
170	Conduction band offsets in CdZnSSe/ZnSSe single quantum wells measured by deep level transient spectroscopy. Applied Physics Letters, 1996, 68, 3591-3593.	1.5	3
171	Adatom migration effects during molecular beam epitaxial growth of InGaAs/GaAs quantum wells on patterned substrates with vertical sidewalls: Blue shift in luminescence spectra. Applied Physics Letters, 1996, 68, 1120-1122.	1.5	6
172	Large blueshift in the photoluminescence of pseudomorphic InGaAs/GaAs quantum wells grown in patterned (100) GaAs grooves and ridges with vertical sidewalls. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1996, 14, 2312.	1.6	4
173	Room temperature operation of MBE self-organized InGaAs quantum dot lasers. , 0, , .		0
174	Room temperature luminescence and 1 1/4µm junction laser operation of In/sub x/Ga/sub 1-x/As/GaAs quantum boxes formed by self-organized molecular beam. , 0, , .		0
175	Room temperature self-organized quantum dot transistors. , 0, , .		1
176	Growth and properties of self-organized In/sub 0.4/Ga/sub 0.6/As-GaAs quantum dot light emitting diodes on silicon substrates. , 0, , .		0